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SPDT SWITCH GaAs MMIC

+2.5~+5.5V

■GENERAL DESCRIPTION

NJG1512V is a GaAs SPDT switch IC featuring high isolation and low insertion loss.

This switch allows low operating voltage from 2.5V at the wide frequency range from 1MHz to 3GHz.

NJG1512V is suitable to switch the synthesizer

signals between transmit and receiving circuit.

A very small SSOP package is adopted.





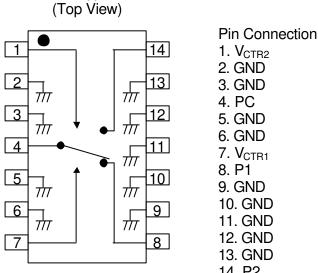
NJG1512V

FEATURES

- •Single, low voltage control
- High isolation
- Low insertion loss
- •Low current consumption
- Package

46dB typ. @f=0.05~2GHz, Pin=0dBm 0.8dB typ. @f=2GHz, Pin=0dBm 2uA typ. @f=0.05~2.5GHz, Pin=10dBm SSOP14 (Mount Size: 6.4x5.0x1.25mm)

■PIN CONFIGURATION



V Type

1. V_{CTB2} 2. GND 3. GND 4. PC 5. GND 6. GND 7. V_{CTB1} 8. P1 9. GND 10. GND 11. GND 12. GND 13. GND 14. P2

TRUTH TABLE

"H"=V_{CTR (H)}, "L"=V_{CTR (L)}

V _{CTR1}	Н	L	L	Н		
V _{CTR2}	L	Н	L	Н		
PC-P1	OFF	ON				
PC-P2	ON	OFF	*1			

*1) Combinations of $V_{CTR1}/V_{CTR2}=L/L$, H/H are not available.



■ABSOLUTE MAXIMUM RATINGS

		$(T_a=25^{\circ}C, Z_s=Z_l=5)$		
PARAMETER	SYMBOL RATINGS		UNITS	
Input Power	P _{in}	27	dBm	
Control Voltage	V _{CTR}	6.0	V	
Power Dissipation	P _D	600	mW	
Operating Temp.	T _{opr}	-20~+85	°C	
Storage Temp.	T _{stg}	-40~+150	°C	

■ELECTRICAL CHARACTERISTICS 1

	-	(TEST CIRCUIT 1: $V_{\text{CTR (L)}}=0V$, $V_{\text{CTR (H)}}=2.7V$, $Z_{\text{s}}=Z_{\text{o}}=50\Omega$, $T_{\text{a}}=25^{\circ}\text{C}$)				
PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS
Control voltage (L)	V _{CTR (L)}	f=0.05~2.5GHz, P _{in} =10dBm	-0.2	0	0.2	V
Control voltage (H)	V _{CTR (H)}	f=0.05~2.5GHz, P _{in} =10dBm	2.5	2.7	5.5	V
Control current		f=0.05~2.5GHz, P _{in} =10dBm	-	2.0	4.0	uA
Isolation	ISL1	f=0.05~2.0GHz, P _{in} =0dBm	43	46	-	dB
Insertion loss 1	LOSS1	f=1.0GHz, P _{in} =0dBm	-	0.6	1.0	dB
Insertion loss 2	LOSS2	f=2.0GHz, P _{in} =0dBm	-	0.8	1.2	dB
Pin at 1dB compression point	P _{-1dB}	f=2.0GHz	19.0	22.0	-	dBm
VSWR	VSWR	f=0.05~2.5GHz, ON STATE	-	1.2	1.8	
Switching time	T _{SW}	f=0.05~2.5GHz	-	8	-	ns

■ELECTRICAL CHARACTERISTICS 2

Insertion loss 3

LOSS3

		(TEST CIRCUIT 2: V _{CTR (L)} =0V,	V _{CTR (H)} =	2.7V, Z _s =	$Z_0=50\Omega$,	T _a =25°C)
PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS
Isolation 2	ISL2	f=1~100MHz, P _{in} =0dBm	-	55	-	dB

0.5

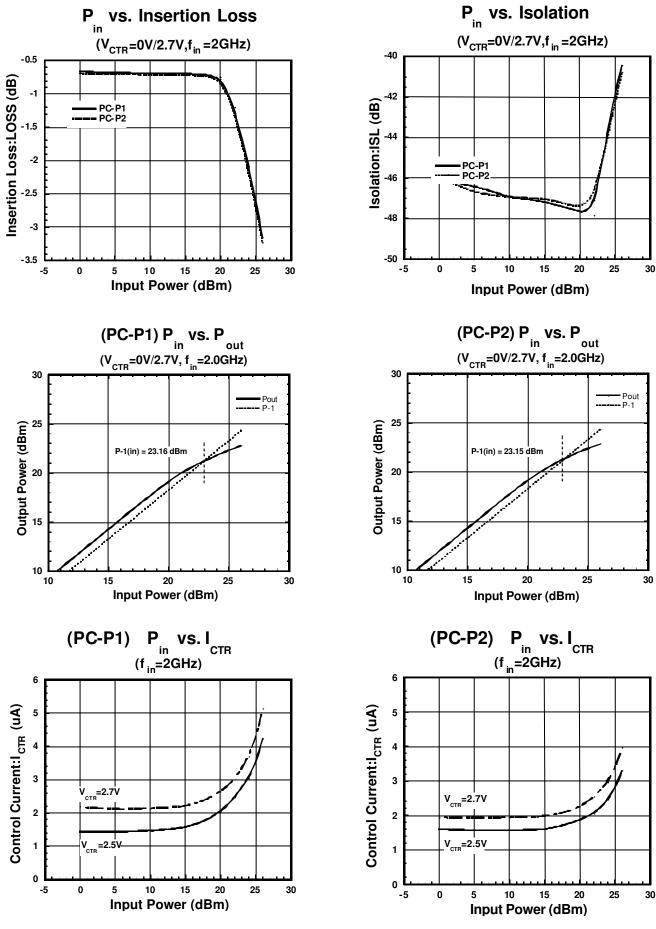
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dB

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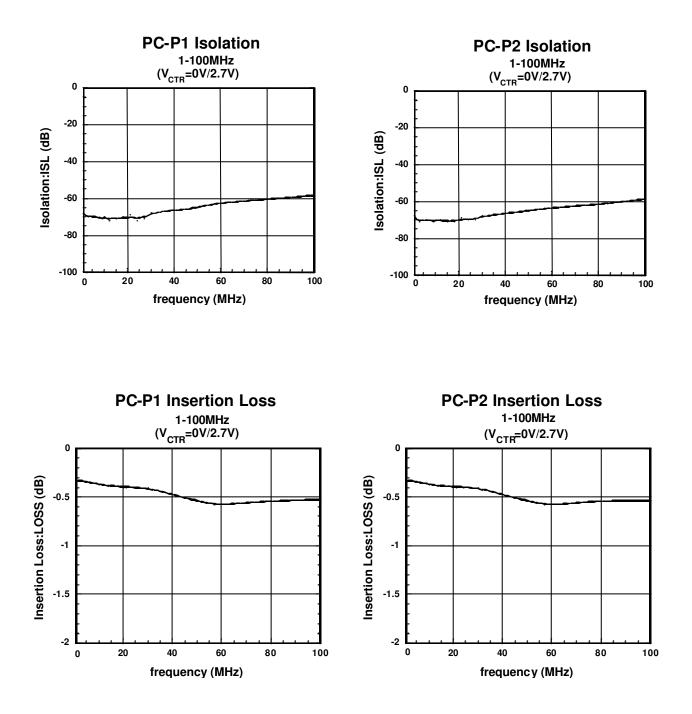
f=1~100MHz, P_{in}=0dBm

■TYPICAL CHARACTERISTICS

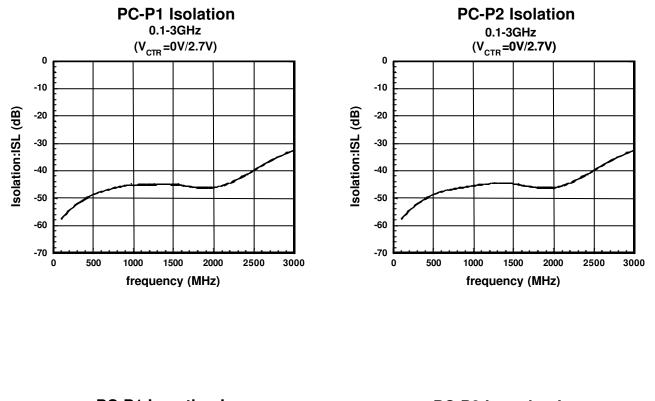


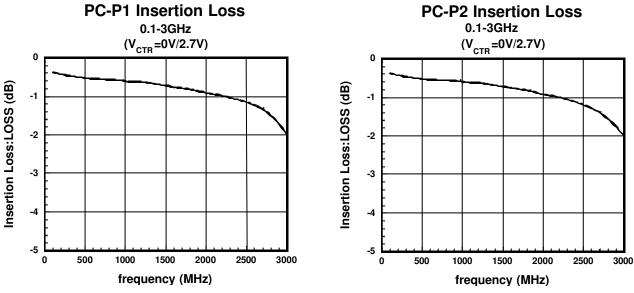
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TYPICAL CHARACTERISTICS



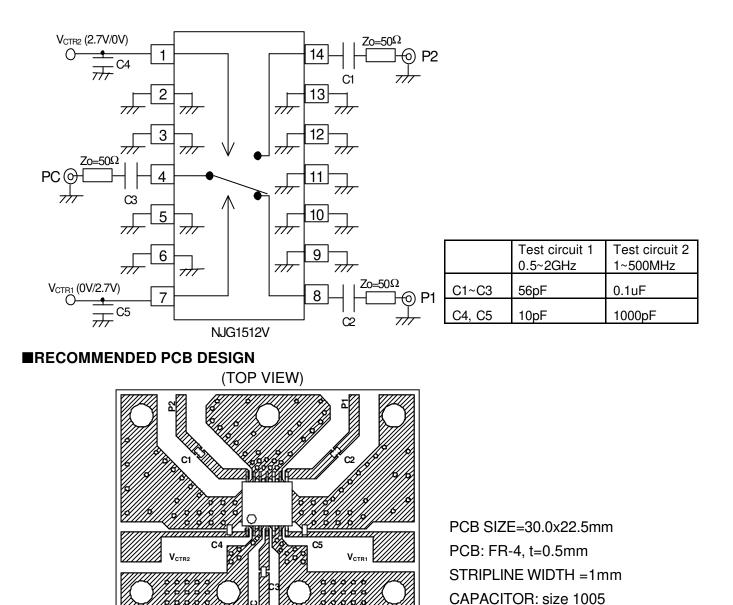
■TYPICAL CHARACTERISTICS





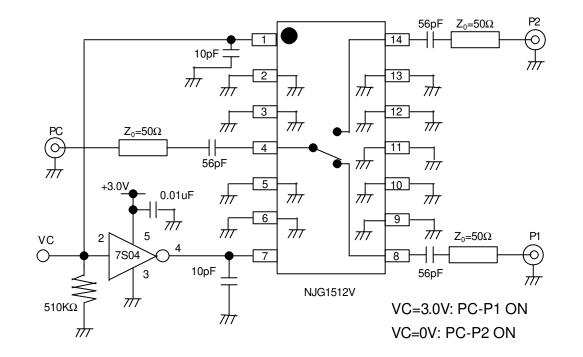
■APPLICATION CIRCUIT: Single control signal operation by using C-MOS inverter

(frequency range: 0.1~2.0GHz)



PRECAUTIONS

- [1] The external capacitors should be connected to the input and output RF terminals (P₁, P₂, P_c) to block DC current. Please use a 0.01uF capacitor at 50 to 100MHz, a 0.1uF capacitor at 100 to 500MHz, and 56pF at 500MHz to 2.0GHz.
- [2] To avoid coupling between terminals, the capacitors have to be placed at the control terminals (V_{CTR1}, V_{CTR2}) as close as possible. The capacitor values of 0.01uF at 50 to 100MHz, 100pF at 100 to 500MHz, and 10pF at 500MHz to 2GHz are desired. In general, the switching time is depend on the capacitor values, so please be careful choosing capacitor values.
- [3] For good isolation characteristics, the ground terminals (2, 3, 5, 6, 9~13 pin) should be directly connected to the ground patterns and through-holes as close as possible using relatively wide patterns.

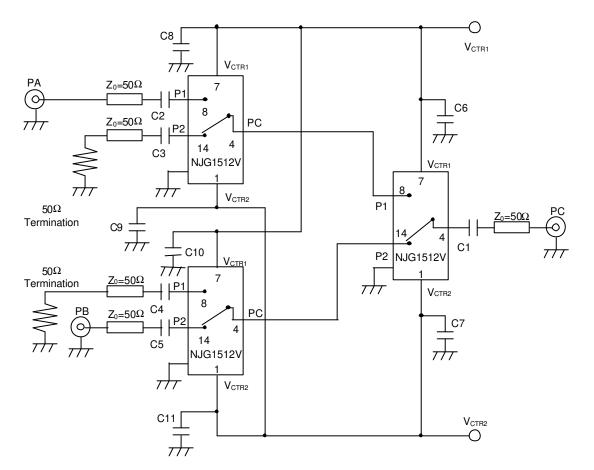


■APPLICATION CIRCUIT 1: Single control signal operation by using C-MOS inverter (frequency: 0.1~2.0GHz)

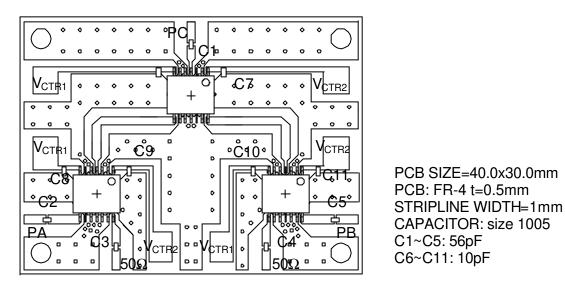
[1]Please connect the bypass capacitor to the power supply terminal of the C-MOS inverter.
[2]In order to stabilize the input impedance of inverter, the input terminal of the C-MOS inverter should be pulled down by the resistor of 510KΩ to the ground plane.

■APPLICATION CIRCUIT 2: High Isolation SPDT Switch

(PA to PC, PB to PC, and PA to PB Isolation are greater than 70dB@fin=0.7~2GHz)



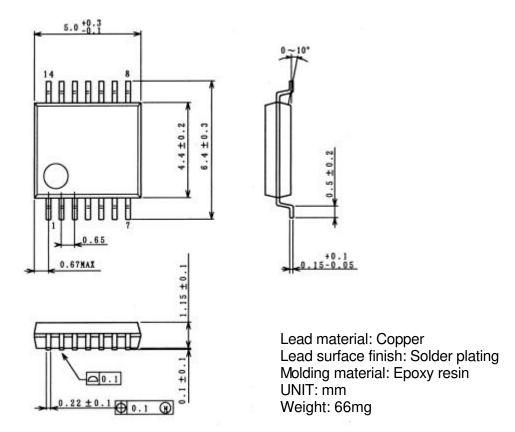
■PCB DESIGN



NOTE: As shown in the schematic above, the two 50Ω ports should be terminate externally.

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PACKAGE OUTLINE (SSOP14)



Cautions on using this product

This product contains Gallium-Arsenide (GaAs) which is a harmful material.

- Do NOT eat or put into mouth.
- Do NOT dispose in fire or break up this product.
- Do NOT chemically make gas or powder with this product.
- To waste this product, please obey the relating law of your country.

This product may be damaged with electric static discharge (ESD) or spike voltage. Please handle with care to avoid these damages.

[CAUTION]

The specifications on this databook are only given for information, without any guarantee as regards either mistakes or omissions. The application circuits in this databook are described only to show representative usages of the product and not intended for the guarantee or permission of any right including the industrial rights.